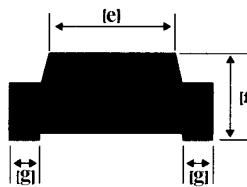
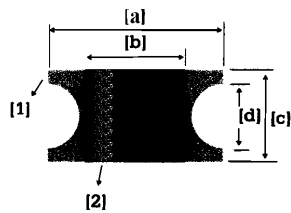




500 mW SURFACE MOUNT EPITAXIAL PLANAR DIODE

Mechanical Dimensions



- a 2.0 unit=mm
- b 1.2 +- .1mm
- c 1.2
- d 0.5
- e 1.0
- f 1.0
- g 0.4

- 1 Termination-Gold Plated on Nickel
- 2 Cathode Band

BPSM4448

Features

- PLANAR PROCESS
- LOW COST LOW PROFILE PACKAGE
- 500 mW POWER DISSIPATION
- MEETS UL SPECIFICATION 94V-0

	BPSM4148	Units
Maximum Ratings		
Peak Reverse Voltage... V_{RM}	100	Volts
RMS Reverse Voltage... $V_{R(rms)}$	75	Volts
Average Forward Rectified Current... I_o	150	mAmps
Non-Repetitive Peak Forward Surge Current... I_{FSM}	500	mAmps
Power Dissipation... P_D	500	mW
Operating Temperature Range... T_J	-25 to 85	°C
Storage Temperature Range... T_{STRG}	-55 to 165	°C
Electrical Characteristics		
Maximum Forward Voltage... V_F @ $I_f = 100$ mA	1.0	Volts
Maximum DC Reverse Current... I_R @ $V_R = 75$ v	5.0	μAmps
Maximum Frequency... f	100	MHz
Maximum Diode Capacitance... C_D	4.0	pF
Maximum Reverse Recovery Time... T_{RR}	4.0	ns

